

DTC143T

NPN SILICON TRANSISTOR

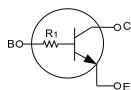
NPN DIGITAL TRANSISTOR (BUILT- IN BIAS RESISTORS)

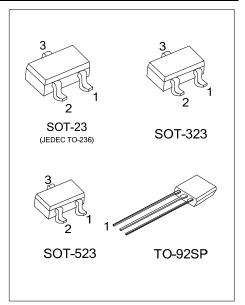
FEATURES

* Built-in bias resistors that implies easy ON/OFF applications.

* The bias resistors are thin-film resistors with complete isolation to allow negative input.

EQUIVALENT CIRCUIT

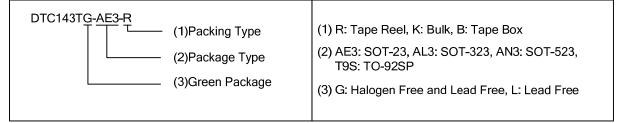




ORDERING INFORMATION

Ordering Number		Deekeese	Pin	Assignr	Decking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	DTC143TG-AE3-R	SOT-23	Е	В	С	Tape Reel	
-	DTC143TG-AL3-R	SOT-323	E	В	С	Tape Reel	
-	DTC143TG-AN3-R	SOT-523	Е	В	С	Tape Reel	
DTC143TL-T9S-B	DTC143TG-T9S-B	TO-92SP	Е	С	В	Tape Box	
DTC143TL-T9S-K	DTC143TG-T9S-K	TO-92SP	Е	С	В	Bulk	

Note: Pin Assignment: E: Emitter B: Base C: Collector



MARKING

SOT-23 / SOT-323 / SOT-523	TO-92SP			
CE3T E E	UTC TC143T G: Halogen Free Data Code			

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	50	V
Collector-Emitter Voltage		V _{CEO}	50	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		Ι _C	100	mA
Collector Power Dissipation	SOT-523	Pc	150	
	SOT-23/SOT-323		200	mW
	TO-92SP		550	
Junction Temperature		ТJ	+150	°C
Storage Temperature		T _{STG}	-55~+150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

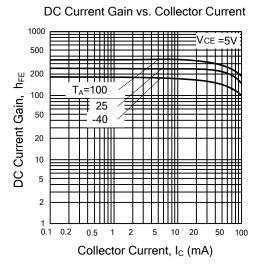
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified.)

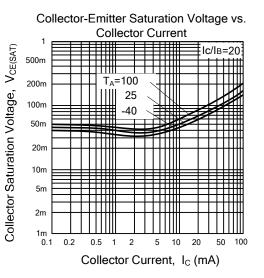
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =50μA	50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA	50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =50μA	5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =50V			0.5	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =4V			0.5	μA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =5mA, I _B =0.25mA			0.3	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1mA	100	250	600	
Input Resistance	R ₁		3.29	4.7	6.11	kΩ
Transition Frequency	f⊤	V _{CE} =10V, I _E =5mA, f=100MHz (Note)		250		MHz

Note: Transition frequency of the device.



TYPICAL CHARACTERISTICS





UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

